

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	(pole adj tip) with (etching adj rate)	USPAT; JPO; DERWENT	OR	ON	2005/11/14 09:01
L2	1	(US-5687045-\$.did.	USPAT	OR	ON	2005/11/14 09:01
L3	1	2 and (ion adj mill\$3)	USPAT; JPO; DERWENT	OR	ON	2005/11/14 09:01
L5	3205	(inert adj gas) near Ar	USPAT; JPO; DERWENT	OR	ON	2005/11/14 09:13
L6	2	(inert adj gas) near Ar near (ion adj mill\$3)	USPAT; JPO; DERWENT	OR	ON	2005/11/14 09:13
S1	825	29/603.11,603.13-603.16,603.18.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:48
S4	5300	427/127,128.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/02/10 08:19
S5	594	451/4,51.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/02/10 08:19
S6	4792	360/121,122,126,317.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:30
S38	1300	204/192.32,192.33,192.35.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:24
S39	1633	204/192.32-192.35.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:25
S40	449	204/192.34.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:25
S41	247	(ion adj milling) with ((pole adj tip) or (pole adj layer))	USPAT; JPO; DERWENT	OR	ON	2005/07/06 10:45
S42	246	(ion adj milling) with (magnetic adj layer)	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:26
S43	27	S41 and S42	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:26
S44	1	S40 and S43	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:26

S45	4	("4208241" "4267013" "6047462" "6591480").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:29
S46	159	S41 and 360/121,122,126,317.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:30
S47	81	S41 and 29/603.11,603.13-603.16,603.18.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:30
S48	44	S46 and S47	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:30
S49	2	S40 and S48	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:30
S50	3	("5116719" "5168409" "5200056").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:32
S51	146	("5438747").URPN.	USPAT	OR	ON	2005/07/03 08:32
S52	21	("5200056").URPN.	USPAT	OR	ON	2005/07/03 08:35
S53	88	mino-tetsuya.in.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:35
S54	8	S41 and S53	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:36
S55	4	S42 and S53	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:36
S56	8	S54 or S55	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:36
S57	4	("4814921" "5438747" "6233116" "6404601").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:36
S58	17	("4639808" "4639811" "5270895" "5285340" "5452163" "5452164" "5508867" "5515221" "5606478" "5621592" "5661621" "5739991" "5812350" "5850325" "5872691" "6151193" "6163442").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:37
S59	53	("5285340").URPN.	USPAT	OR	ON	2005/07/03 08:42
S60	8	("5285340" "5452164" "5649351" "5668689" "5802700" "5805391" "5831801" "6018862").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:51

S61	2	("6188544").PN.	USPAT; USOCR; JPO; DERWENT	OR	OFF	2005/07/03 08:51
S62	516	216/22.ccls.	USPAT; JPO; DERWENT	OR	ON	2005/07/03 08:51
S63	2	("5673163" "5938941").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:53
S64	14	((("5673163") or ("5938941") or ("5639509") or ("5452164") or ("5878481") or ("6320725") or ("4681813"))).PN.	USPAT; USOCR; JPO; DERWENT	OR	OFF	2005/07/03 08:53
S65	2	("5315469" "5493464").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/03 08:56
S66	29	("5639509").URPN.	USPAT	OR	ON	2005/07/03 08:56
S67	19	(etch\$3 adj rate) same (((gap or insulat\$3) adj layer) with (magnetic adj (layer or material)))	USPAT; JPO; DERWENT	OR	ON	2005/07/03 09:05
S69	6	S67 and @ad<"19971015"	USPAT; JPO; DERWENT	OR	ON	2005/07/06 10:45
S70	5	(gap adj layer) near ((silicon adj dioxide) or (tantalum adj oxide) or (silicon adj cardide) or (aluminum adj nitride))	USPAT; JPO; DERWENT	OR	ON	2005/07/03 09:09
S71	13	((pole adj layer) or (pol adj tip)) near (FeN or NiFe)	USPAT; JPO; DERWENT	OR	ON	2005/07/03 09:10
S72	0	S70 and S71	USPAT; JPO; DERWENT	OR	ON	2005/07/03 09:10
S73	18	S70 or S71	USPAT; JPO; DERWENT	OR	ON	2005/07/03 09:11
S74	10	S73 and @ad<"19971015"	USPAT; JPO; DERWENT	OR	ON	2005/07/03 09:11
S75	2	("0461411").PN.	USPAT; USOCR; JPO; DERWENT	OR	OFF	2005/07/06 10:45
S76	88	mino-tetsuya.in.	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:22

S77	8	S76 and ((ion adj milling) with ((pole adj tip) or (pole adj layer)))	USPAT; JPO; DERWENT	OR	ON	2005/07/06 10:45
S78	0	S77 and @ad<"19971015"	USPAT; JPO; DERWENT	OR	ON	2005/07/06 10:45
S79	1746	(first adj magnetic) with (second adj magnetic) with (gap or insulat\$3 or dielectric)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:49
S80	0	(ion adj "mill\$3")	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:49
S81	0	(ion adj "mill\$3") with (active adj gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:50
S82	0	(ion adj "mill\$3") with ((no or without) near (active adj gas))	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:51
S83	0	(ion adj "mill\$3") with ((no or without) near (reactive adj gas))	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:51
S84	0	(ion adj "mill\$3") with (no near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:52
S85	73	(no near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:52
S86	0	(ion adj "mill\$3") same (no near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:52
S87	0	(ion near "mill.inmg") same (no near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:53
S88	0	(ion near "mill.ing") same (no near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:53
S89	0	(ion near milling) same (no near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:53
S90	7017	(ion near milling)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:55
S91	3	S85 and S90	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:54
S92	36841	ion near (milling or etching)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 10:56

S93	6346	etch\$3 near rate near (low\$2 or high\$2)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:03
S94	2096	etch\$3 near rate near different	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:02
S95	480	S93 and S94	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:02
S96	27	(magnetic adj layer) near (non-magnetic) near etch\$3	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:03
S97	0	(magnetic adj layer) near (nonmagnetic) near etch\$3	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:04
S98	1	S95 and S96	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:03
S99	4928	etch\$3 near rate near (equal or high\$2)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:04
S10 0	378	S94 and S99	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:04
S10 1	43	(nonmagnetic) near etch\$3	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:04
S10 2	0	S100 and S101	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:05
S10 3	190	(magnetic adj layer) near etch\$3	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:04
S10 4	4	S101 and S103	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:06
S10 5	1	S99 and S101	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:05
S10 6	13	S99 and S103	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:09
S10 7	9	(etch\$3 near rate) with (magnetic and nonmagnetic)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:15
S10 8	288523	(silicon adj dioxide) or (taatalum adj oxide) or (carbide) or (aluminum adj nitride)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:14

S10 9	294791	(silicon adj dioxide) or (tantalum adj oxide) or (carbide) or (aluminum adj nitride)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:16
S11 0	1607	S99 and S109	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:15
S11 1	6	(etch\$3 near rate) with (magnetic same nonmagnetic)	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:15
S11 2	1	S99 and S111	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:16
S11 3	302	((silicon adj dioxide) or (tantalum adj oxide) or (carbide) or (aluminum adj nitride)) same (etch\$3 near rate near (equal or high\$2))	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:17
S11 4	0	((silicon adj dioxide) or (tantalum adj oxide) or (carbide) or (aluminum adj nitride)) same (etch\$3 near rate near (equal or high\$2)) same ((magnetic same nonmagnetic))	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:17
S11 5	10	((silicon adj dioxide) or (tantalum adj oxide) or (carbide) or (aluminum adj nitride)) same (etch\$3 near rate near (equal or high\$2)) same magnetic	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:17
S11 6	5	S115 and @ad<"19971010"	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:18
S11 7	5	S115 and @ad<"19971015"	USPAT; JPO; DERWENT	OR	ON	2005/10/24 15:18
S11 8	2	("6188544").PN.	USPAT; USOCR; JPO; DERWENT	OR	OFF	2005/10/24 15:22
S11 9	2	("5673163" "5938941").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/24 15:22
S12 0	11	etching with ((no or without) near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/11/14 09:13
S12 1	2	S120 and (ion near mill\$3)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 10:58
S12 2	23	IBAE	USPAT; JPO; DERWENT	OR	ON	2005/11/03 10:58

S12 3	8	S122 and (ion near mill\$3)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:00
S12 4	88	(ion near mill\$3) with inert	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:01
S12 5	109	((no or without) near reactive near gas)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:00
S12 6	0	S124 and S125	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:00
S12 7	15	(ion near mill\$3) near inert	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:20
S12 8	0	(write adj gap) near (tantalum)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:21
S12 9	0	((pole near tip) near gap) near (silicon or tantalum)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 11:21
S13 0	1	(US-5452164-\$).did.	USPAT	OR	ON	2005/11/03 13:26
S13 1	1	S130 and (gap)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:34
S13 2	1	(US-5438747-\$).did.	USPAT	OR	ON	2005/11/03 13:34
S13 3	1	S132 and (gap)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:35
S13 4	16195	etching adj rate	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:43
S13 5	1	(etching adj rate) same (write adj gap)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:43
S13 6	4	(etching adj rate) and tugbang.xa.	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:39
S13 7	9050	Tantalum adj oxide	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:40
S13 8	1	(Tantalum adj oxide) same (write adj gap)	USPAT; JPO; DERWENT	OR	ON	2005/11/03 13:42
S13 9	1	(Tantalum adj oxide) same (write adj gap)	US-PGPUB	OR	ON	2005/11/03 13:42

S14 0	5450	etching adj rate	US-PGPUB	OR	ON	2005/11/03 13:43
S14 1	6	(etching adj rate) same (write adj gap)	US-PGPUB	OR	ON	2005/11/03 13:44
S14 2	34	(etching adj rate) same (insulat\$3 with magnetic)	US-PGPUB	OR	ON	2005/11/03 13:45
S14 3	2	("6188544").PN.	USPAT; USOCR; JPO; DERWENT	OR	OFF	2005/11/03 13:54